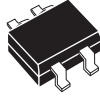


CBRHDSH1-40L
 HIGH DENSITY
 1.0 AMP DUAL IN LINE
 LOW V_F
 SCHOTTKY BRIDGE RECTIFIER

HD BRIDGE



HD DIP CASE

CentralTM
 Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH1-40L type is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING CODE: CSH1

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

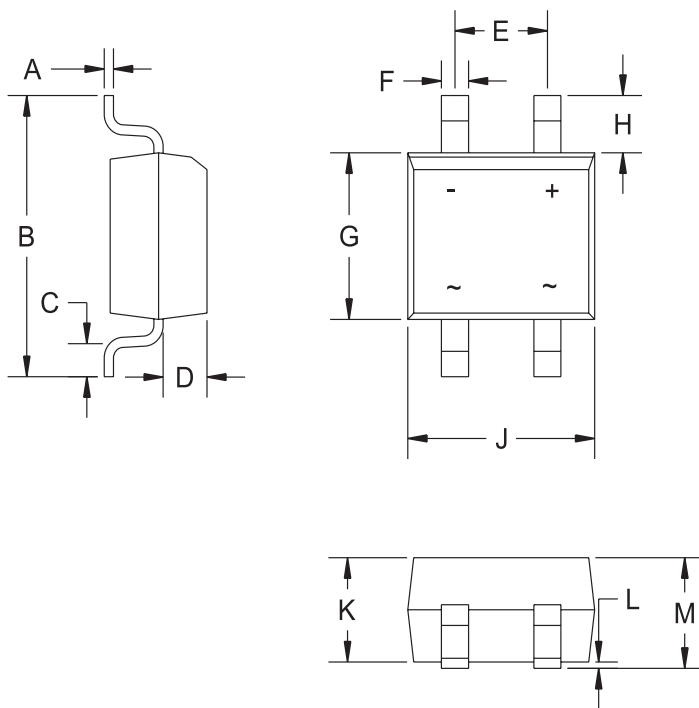
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	I_O	1.0	A
Peak Forward Surge Current	I_{FSM}	20	A
Power Dissipation	P_D	1.2	W
Operating Junction Temperature Range	T_J	-50 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-50 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	85	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=40\text{V}$	20	50	μA
I_R	$V_R=40\text{V}, T_A=100^\circ\text{C}$	5.0	20	mA
V_F	$I_F=500\text{mA}$	360	380	mV
V_F	$I_F=1.0\text{A}$	390	440	mV
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$	150		pF

R1 (23-May 2006)

HD DIP CASE - MECHANICAL OUTLINE



R1

MARKING CODE: CSH1

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.276	-	7.00
C	0.028	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.091	0.106	2.30	2.70
F	0.020	0.031	0.50	0.80
G	0.142	0.157	3.60	4.00
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.091	0.106	2.30	2.70
L	-	0.008	-	0.20
M	-	0.118	-	3.00

HD DIP (REV: R1)

R1 (23-May 2006)